

Applicant : Shinji KAWASAKI et al.
Serial No. : National Phase of PCT/JP2004/003738
Filed : September 16, 2005
Page : 3 of 10

Attorney's Docket No.: 28953.7283

Amendments to the Specification:

Prior to examination, please amend the specification as follows.

Please insert a new paragraph beginning at page 1, line 6, as follows:

--CLAIM OF PRIORITY

--This application claims priority under 35 USC 371 of International Application No. PCT/JP2004/003738, filed on March 19, 2004, which claims priority of Japanese Patent Application No. 2003-078412, filed on March 20, 2003, the entire contents of which are hereby incorporated by reference.--

Please amend the paragraph beginning at page 4, line 1, as follows:

[8] A method for producing a porous material according to [7], wherein, after preparing the silicon-silicon carbide porous material, the atmosphere used therein is changed to a nitrogen atmosphere without lowering the temperature to room temperature and keeping the temperature at 1,200°C or more, and nitriding and firing the silicon-~~nitride~~-silicon carbide porous material at 1,200 to 1,800°C in the nitrogen atmosphere is conducted.